



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Philip L. Hower, et al. Docket No: TI-30010  
Serial No: 10/036,323 Conf. No: 3224  
Examiner: Thomas L. Dickey Art Unit: 2826  
Filed: 12/31/2001  
For: N-CHANNEL LDMOS WITH BURIED P-TYPE REGION TO PREVENT PARASITIC  
BIPOLAR EFFECTS

**LETTER TO OFFICIAL DRAFTSPERSON**

Commissioner For Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450  
  
Attention: Official Draftsperson

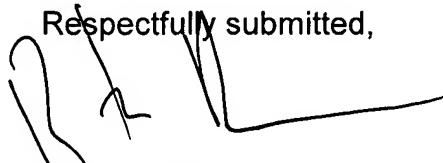
**MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(a)**  
I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 7-18-05.

  
Ann Trent

Dear Sir:

Transmitted herewith for filing are six replacement sheets of corrected formal drawings for the above identified application. Charge any necessary fees to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.

Respectfully submitted,



Peter K. McLarty  
Attorney for Applicants  
Reg. No. 44,923

Texas Instruments Incorporated  
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(972) 917-4258



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ATTORNEY: PKM  
DOCKET NO: TL30010  
DATE: 6-1-5  
DUE DATE: 6-2-5

*TEXAS INSTRUMENTS  
PATENT DRAFTING*

*Michael Jenkins*  
972-917-5639

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